# N-Channel 150-V (D-S) MOSFET

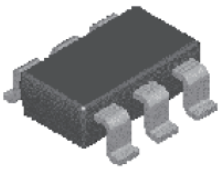
**Key Features:**
- Low $r_{DS(on)}$ trench technology
- Low thermal impedance
- Fast switching speed

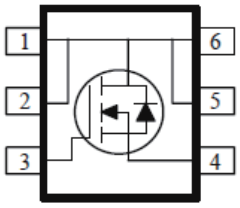
**Typical Applications:**
- PoE PSE and PD Circuits
- LED Inverter Circuits
- 48V-Input DC/DC Conversion Circuits

| PRODUCT SUMMARY | | |
|---|---|---|
| $V_{DS}$ (V) | $r_{DS(on)}$ (mΩ) | $I_D$ (A) |
| 150 | 245 @ $V_{GS}$ = 10V | 2.4 |
| | 288 @ $V_{GS}$ = 4.5V | 2.2 |

Pb-free
RoHS COMPLIANT
HALOGEN FREE

TSOP-6






| ABSOLUTE MAXIMUM RATINGS ($T_A$ = 25°C UNLESS OTHERWISE NOTED) | | | | |
|---|---|---|---|---|
| **Parameter** | | **Symbol** | **Limit** | **Units** |
| Drain-Source Voltage | | $V_{DS}$ | 150 | V |
| Gate-Source Voltage | | $V_{GS}$ | ±20 | |
| Continuous Drain Current [a] | $T_A$=25°C | $I_D$ | 2.4 | A |
| | $T_A$=70°C | | 1.9 | |
| Pulsed Drain Current [b] | | $I_{DM}$ | 8 | |
| Continuous Source Current (Diode Conduction) [a] | | $I_S$ | 2.6 | A |
| Power Dissipation [a] | $T_A$=25°C | $P_D$ | 2 | W |
| | $T_A$=70°C | | 1.3 | |
| Operating Junction and Storage Temperature Range | | $T_J$, $T_{stg}$ | -55 to 150 | °C |

| THERMAL RESISTANCE RATINGS | | | | |
|---|---|---|---|---|
| **Parameter** | | **Symbol** | **Maximum** | **Units** |
| Maximum Junction-to-Ambient [a] | t <= 10 sec | $R_{\theta JA}$ | 62.5 | °C/W |
| | Steady State | | 110 | |

Notes

a. Surface Mounted on 1” x 1” FR4 Board.

b. Pulse width limited by maximum junction temperature

## Electrical Characteristics

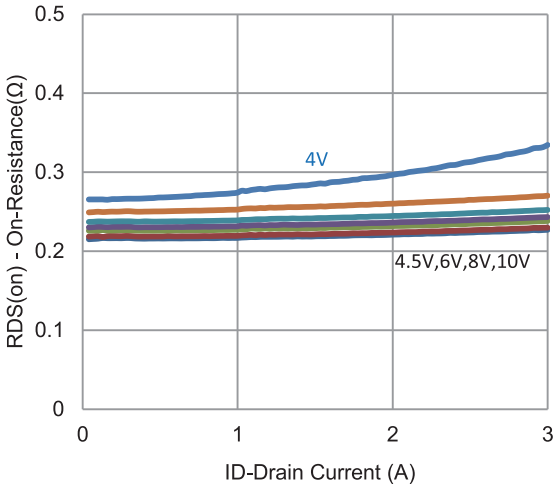
| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| **Static** | | | | | | |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS}$ = $V_{GS}$, $I_D$ = 250 uA | 1 | | | V |
| Gate-Body Leakage | $I_{GSS}$ | $V_{DS}$ = 0 V, $V_{GS}$ = ±20 V | | | ±100 | nA |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{DS}$ = 120 V, $V_{GS}$ = 0 V | | | 1 | uA |
| | | $V_{DS}$ = 120 V, $V_{GS}$ = 0 V, $T_J$ = 55°C | | | 10 | |
| On-State Drain Current [a] | $I_{D(on)}$ | $V_{DS}$ = 5 V, $V_{GS}$ = 10 V | 3.5 | | | A |
| Drain-Source On-Resistance [a] | $r_{DS(on)}$ | $V_{GS}$ = 10 V, $I_D$ = 2 A | | | 245 | mΩ |
| | | $V_{GS}$ = 4.5 V, $I_D$ = 1.6 A | | | 288 | |
| Forward Transconductance [a] | $g_{fs}$ | $V_{DS}$ = 15 V, $I_D$ = 2 A | | 8 | | S |
| Diode Forward Voltage [a] | $V_{SD}$ | $I_S$ = 1.3 A, $V_{GS}$ = 0 V | | 0.77 | | V |
| **Dynamic [b]** | | | | | | |
| Total Gate Charge | $Q_g$ | $V_{DS}$ = 75 V, $V_{GS}$ = 4.5 V, $I_D$ = 2 A | | 4 | | nC |
| Gate-Source Charge | $Q_{gs}$ | | | 1.1 | | |
| Gate-Drain Charge | $Q_{gd}$ | | | 2.4 | | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DS}$ = 75 V, $R_L$ = 37.5 Ω, $I_D$ = 2 A, $V_{GEN}$ = 10 V, $R_{GEN}$ = 6 Ω | | 4 | | ns |
| Rise Time | $t_r$ | | | 7 | | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | 18 | | |
| Fall Time | $t_f$ | | | 7 | | |
| Input Capacitance | $C_{iss}$ | $V_{DS}$ = 15 V, $V_{GS}$ = 0 V, f = 1 Mhz | | 324 | | pF |
| Output Capacitance | $C_{oss}$ | | | 42 | | |
| Reverse Transfer Capacitance | $C_{rss}$ | | | 21 | | |

Notes

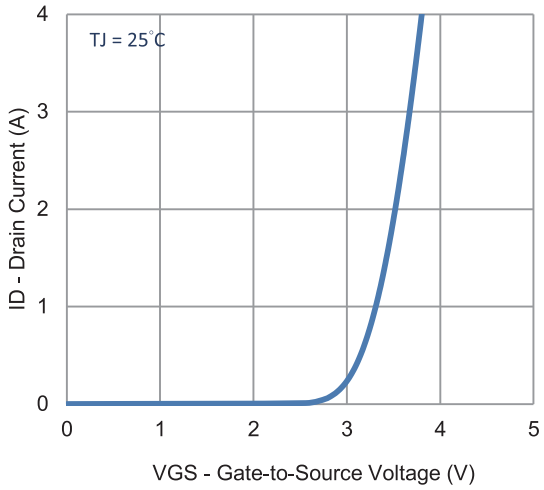
a. Pulse test: PW <= 300us duty cycle <= 2%.

b. Guaranteed by design, not subject to production testing.

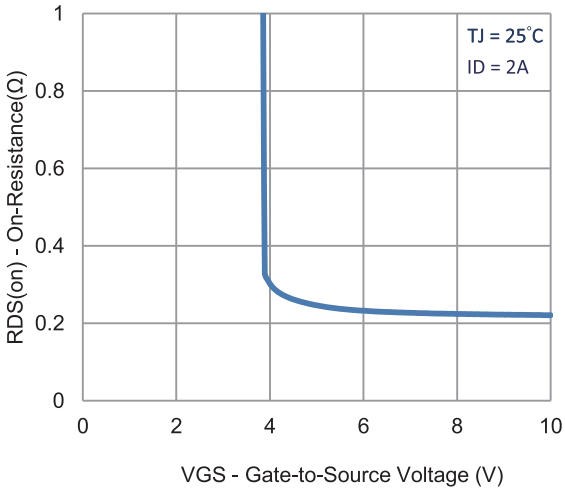
## Typical Electrical Characteristics



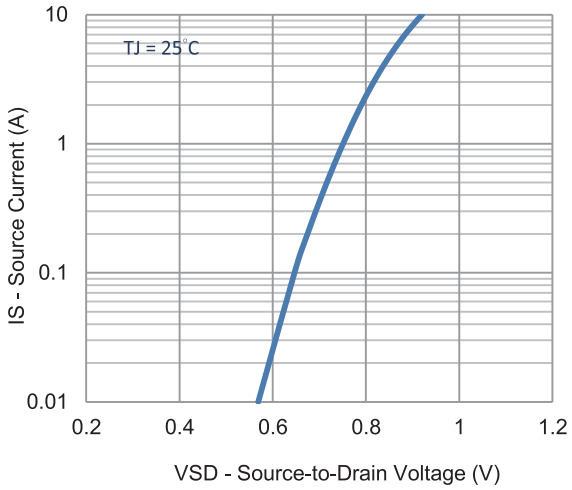

**1. On-Resistance vs. Drain Current**



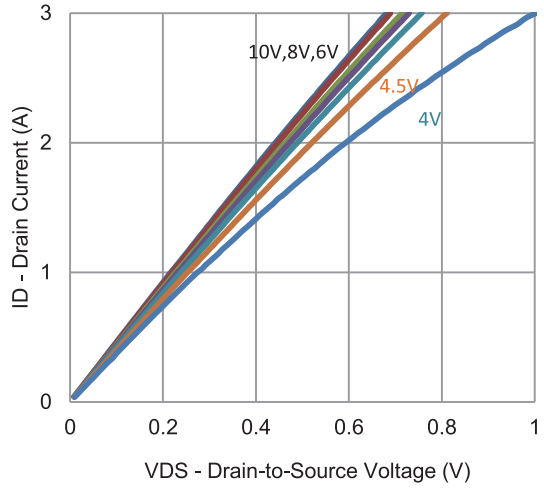

**2. Transfer Characteristics**



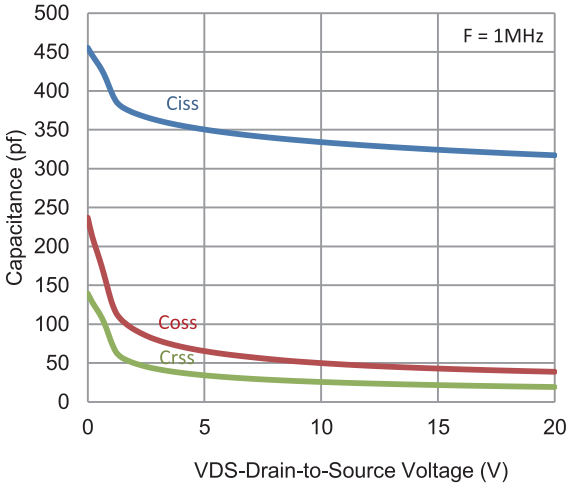

**3. On-Resistance vs. Gate-to-Source Voltage**




**4. Drain-to-Source Forward Voltage**

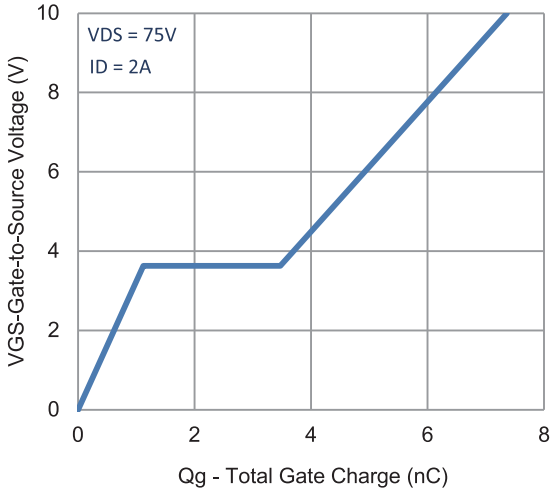



**5. Output Characteristics**

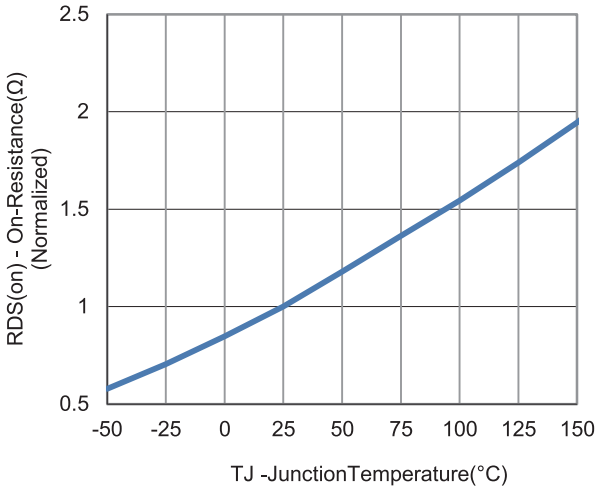



**6. Capacitance**

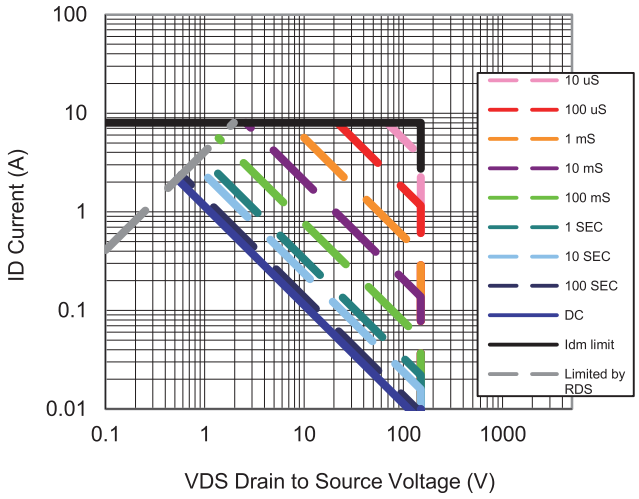
## Typical Electrical Characteristics



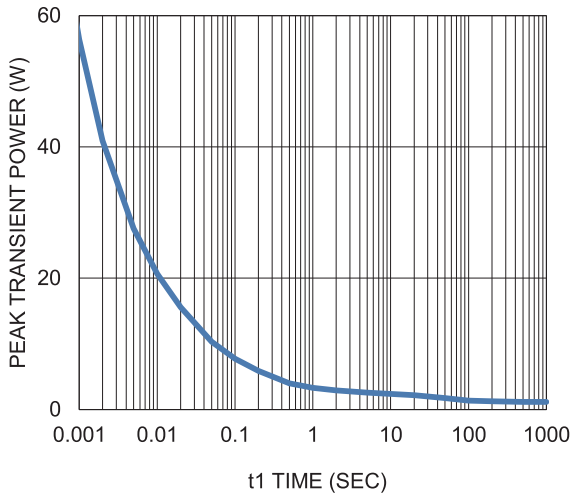

**7. Gate Charge**



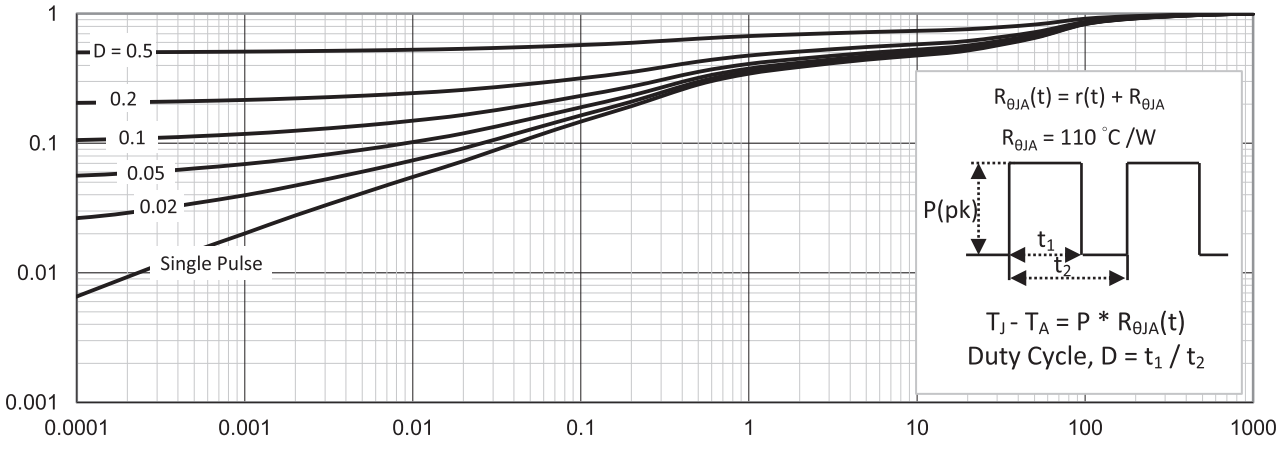

**8. Normalized On-Resistance Vs Junction Temperature**




**9. Safe Operating Area**

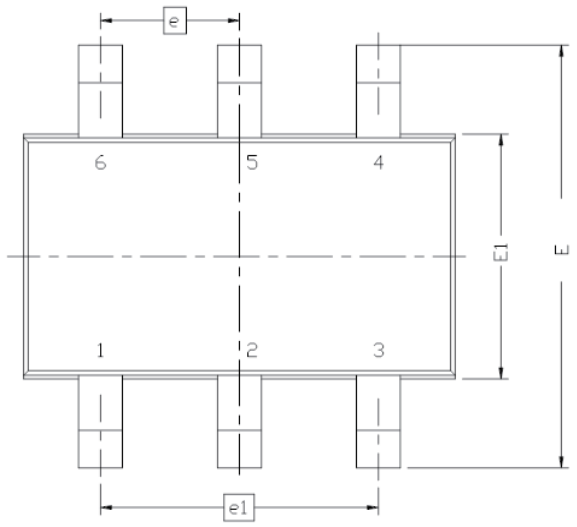



**10. Single Pulse Maximum Power Dissipation**

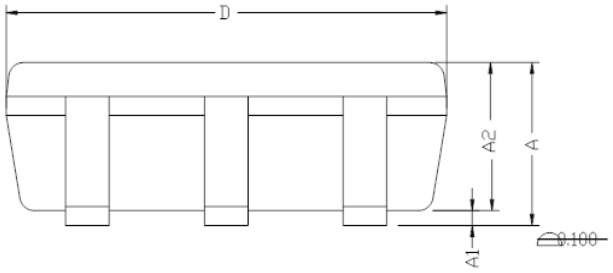


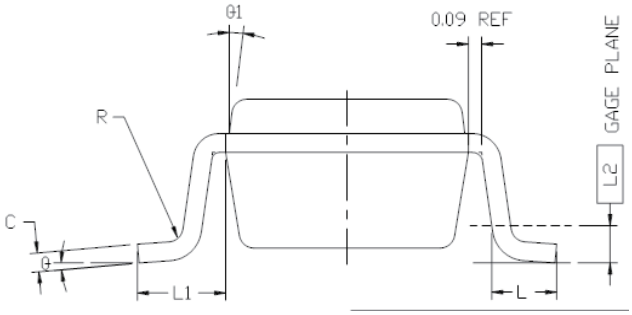

**11. Normalized Thermal Transient Junction to Ambient**

## Package Information




| DIM. | MILLIMETERS | | |
|---|---|---|---|
| | MIN | NOM | MAX |
| A | 0.935 | --- | 1.10 |
| A1 | 0.01 | --- | 0.10 |
| A2 | 0.70 | --- | 1.00 |
| b | 0.25 | 0.32 | 0.40 |
| c | 0.10 | 0.15 | 0.20 |
| D | 2.95 | 3.05 | 3.10 |
| E | 2.70 | 2.85 | 2.98 |
| E1 | 1.55 | 1.65 | 1.70 |
| e | 0.95 BSC | | |
| L | 0.30 | --- | 0.60 |
| L1 | 0.60REF | | |
| L2 | 0.25BSC | | |
| R | 0.10 | --- | --- |
| θ | 0° | 4° | 8° |
| θ1 | 7° NOM | | |




Note:

1. All Dimension Are In mm.
2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Tie Bar Burrs, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.
4. The Package Top May Be Smaller Than The Package Bottom.
5. Dimension "B" Does Not Include Dambar Protrusion. Allowable Dambar Protrusion Shall Be 0.08 mm Total In Excess Of "B" Dimension At Maximum Material Condition. The Dambar Cannot Be Located On The Lower Radius Of The Foot.